



# 7-13  
1/8/03  
Mallish

Atty. Docket No. 8029-1041

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PATENTS

JAN-3 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

TECHNOLOGY CENTER 2800

In re application of

Masaru TSUKIJI

Confirmation No. 4695

Serial No. 09/761,693

GROUP 2826

Filed January 18, 2001

Examiner Fetsum Abraham

STRUCTURE AND MANUFACTURING  
METHOD OF NON-VOLATILE FLASH  
MEMORY

AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

*File*  
*for*

Responsive to the Official Action of October 21, 2002,  
please amend the above-identified application as follows:

IN THE CLAIMS:

Amend claim 3 as follows:

--3. (amended) A structure of a non-volatile flash  
memory that is a NOR type non-volatile flash memory, provides  
floating gates and a common source line, wherein:

an impurity gradient distribution of a source in a  
memory cell adjacent to where said source joins a semiconductor  
substrate is gradual.--

REMARKS

The indication that claims 1-2 and 4-12 have been  
allowed is acknowledged with thanks. Claim 3 was rejected under